High-Current Complementary Silicon Transistors

... for use as output devices in complementary general purpose amplifier applications.

- High DC Current Gain hFE = 1000 (Min) @ IC 20 Adc
- Monolithic Construction with Built-in Base Emitter Shunt Resistor
- Junction Temperature to +200°C

MAXIMUM RATINGS

Rating	Symbol	MJ11012	MJ11013 MJ11014	MJ11015 MJ11016	Unit
Collector-Emitter Voltage	VCEO	60	90	120	Vdc
Collector-Base Voltage	V _{CB}	60	90	120	Vdc
Emitter-Base Voltage	V _{EB}	5			Vdc
Collector Current	Ic	30			Adc
Base Current	IB	1			Adc
Total Device Dissipation @T _C = 25°C Derate above 25°C @ T _C = 100°C	PD	200 1.15			Watts W/°C
Operating Storage Junction Temperature Range	TJ, Tstg	-55 to +200			°C

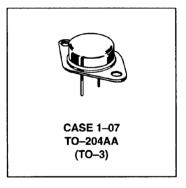
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	ReJC	0.87	°C/W
Maximum Lead Temperature for Soldering Purposes for ≤ 10 Seconds.	TL	275	°C

MJ11013 MJ11015 MJ11012 MJ11014 MJ11016*

*Motorola Preferred Device

30 AMPERE
DARLINGTON
POWER TRANSISTORS
COMPLEMENTARY
SILICON
60-120 VOLTS
200 WATTS



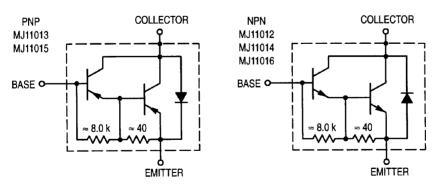


Figure 1. Darlington Circuit Schematic

Preferred devices are Motorola recommended choices for future use and best overall value.

MJ11013 MJ11015 MJ11012 MJ11014 MJ11016

ELECTRICAL CHARACTERISTICS ($T_C = 25$ °C unless otherwise noted.)

Characteristics		Symbol	Min	Max	Unit
OFF CHARACTERISTICS				<u> </u>	•
Collector–Emitter Breakdown Voltage(1) (I _C = 100 mAdc, I _B = 0)	MJ11012 MJ11013, MJ11014 MJ11015, MJ11016	V(BR)CEO	60 90 120	_ _ _	Vdc
Collector-Emitter Leakage Current (VCE = 60 Vdc, RBE = 1k ohm) (VCE = 90 Vdc, RBE = 1k ohm) (VCE = 120 Vdc, RBE = 1k ohm) (VCE = 60 Vdc, RBE = 1k ohm, TC = 150°C) (VCE = 90 Vdc, RBE = 1k ohm, TC = 150°C) (VCE = 120 Vdc, RBE = 1k ohm, TC = 150°C)	MJ11012 MJ11013, MJ11014 MJ11015, MJ11016 MJ11012 MJ11013, MJ11014 MJ11015, MJ11016	ICER	 - - - -	1 1 1 5 5 5	mAdc
Emitter Cutoff Current (VBE = 5 Vdc, I _C = 0)		¹ EBO		5	mAdc
Collector–Emitter Leakage Current (V _{CE} = 50 Vdc, I _B = 0)		ICEO	_	1	mAdc
ON CHARACTERISTICS(1)					
DC Current Gain (I _C = 20 Adc, V _{CE} = 5 Vdc) (I _C = 30 Adc, V _{CE} = 5 Vdc)		hFE	1000 200		_
Collector–Emitter Saturation Voltage (I _C = 20 Adc, I _B = 200 mAdc) (I _C = 30 Adc, I _B = 300 mAdc)		VCE(sat)	<u>-</u>	3 4	Vdc
Base–Emitter Saturation Voltage (I _C = 20 A, I _B = 200 mAdc) (I _C = 30 A, I _B = 300 mAdc)		V _{BE(sat)}		3.5 5	Vdc
DYNAMIC CHARACTERISTICS					
Current-Gain Bandwidth Product (I _C = 10 A, V _{CE} = 3 Vdc, f = 1 MHz)		h _{fe}	4		MHz

⁽¹⁾ Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

MJ11013 MJ11015 MJ11012 MJ11014 MJ11016

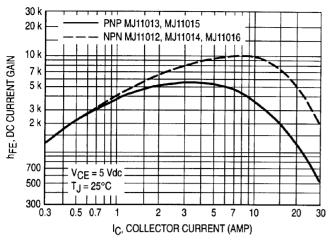


Figure 2. DC Current Gain (1)

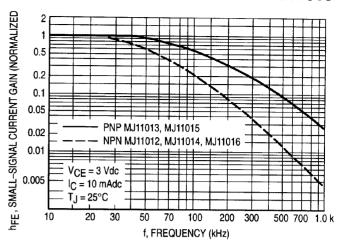


Figure 3. Small-Signal Current Gain

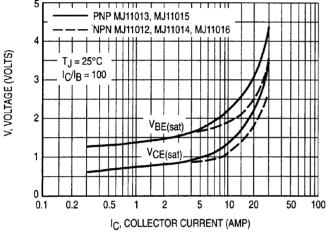


Figure 4. "On" Voltages (1)

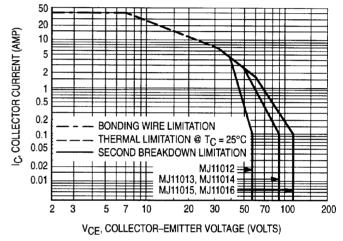


Figure 5. Active Region DC Safe Operating Area

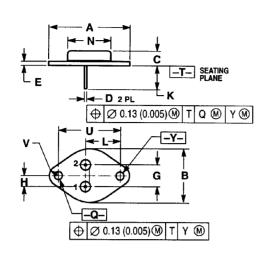
There are two limitations on the power handling ability of a transistor average junction temperature and secondary breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operations e.g., the transistor must not be subjected to greater

dissipation than the curves indicate.

At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by secondary breakdown.

MJ11013 MJ11015 MJ11012 MJ11014 MJ11016

PACKAGE DIMENSIONS



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INCHES		MILLIMETERS			
DIM	MIN	MAX	MIN	MAX		
Α	1.550	1,550 REF		39.37 REF		
В		1.050	_	26.67		
С	0.250	0.335	6.35	8.51		
D	0.038	0.043	0.97	1.09		
Е	0.055	0.070	1.40	1.77		
G	0.430	BSC	10.92 BSC			
Н	0.215	BSC	5,46	BSC		
K	0.440	0.480	11.18	12.19		
L	0.665	BSC	16.89	BSC		
N		0.830	1	21.08		
O	0.151	0.165	3.84	4.19		
U	1.187	BSC	30.15	BSC		
. V	0.131	0.188	3.33	4.77		

STYLE 1: PIN 1. BASE 2 EMITTER CASE: COLLECTOR

CASE 1-07 TO-204AA (TO-3) **ISSUE Z**

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters can and do vary in different applications. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of systems interface for surjucial implication in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and (A) are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

How to reach us: USA/EUROPE: Motorola Literature Distribution;

P.O. Box 20912; Phoenix, Arizona 85036. 1-800-441-2447

MFAX: RMFAX0@email.sps.mot.com - TOUCHTONE (602) 244-6609 INTERNET: http://Design-NET.com

JAPAN: Nippon Motorola Ltd.; Tatsumi-SPD-JLDC, Toshikatsu Otsuki, 6F Seibu-Butsuryu-Center, 3-14-2 Tatsumi Koto-Ku, Tokyo 135, Japan. 03-3521-8315

HONG KONG: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298



